



First Named Inventor	Leonard Forbes	INFORMATION DISCLOSURE STATEMENT FORM PTO-1449
Serial No.	10719,772	
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Examiner Name	Unknown	
Confirmation No.	2900	
Attorney Docket No.	400.252US01	
Title: APPARATUS AND METHOD FOR SPLIT GATE NROM MEMORY		Sheet 1 of 7

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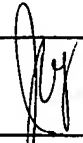


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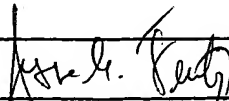
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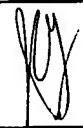

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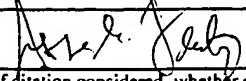
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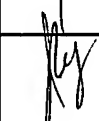
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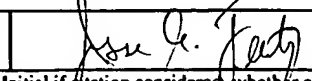
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